# onsemi

## **Bipolar Transistor**

50 V, 10 A, Low V<sub>CE</sub>(sat), NPN TO-220F-3FS

## 2SC6144SG

#### Features

- Adoption of MBIT Process
- Large Current Capacitance  $(I_C = 10 \text{ A})$
- Low Collector-to-Emitter Saturation Voltage (V<sub>CE</sub>(sat) = 180 mV(typ.))
- High-speed Switching (t<sub>f</sub> = 25 ns(typ.))

#### Applications

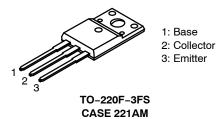
• Relay Drivers, Lamp Drivers, Motor Drivers

#### Specifications

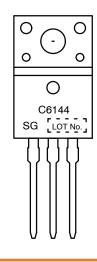
#### ABSOLUTE MAXIMUM RATINGS at Ta = 25°C

| Parameter                       | Symbol           | Conditions   | Ratings     | Units |
|---------------------------------|------------------|--|-------------|-------|
| Collector-to-Base<br>Voltage    | V <sub>CBO</sub> |  | 60          | V     |
| Collector-to-Emitter<br>Voltage | V <sub>CEO</sub> |  | 50          | V     |
| Emitter-to-Base Voltage         | V <sub>EBO</sub> |  | 5           | V     |
| Collector Current               | Ι <sub>C</sub>   |  | 10          | А     |
| Collector Current (Pulse)       | I <sub>CP</sub>  |  | 13          | А     |
| Base Current                    | Ι <sub>Β</sub>   |  | 2           | А     |
| Collector Dissipation           | P <sub>C</sub>   | $\begin{array}{l} T_C = 25^\circ C, \\ P_T \leq 1 \ s \end{array}$ | 25          | W     |
| Junction Temperature            | Тj               |  | 150         | °C    |
| Storage Temperature             | T <sub>stg</sub> |  | –55 to +150 | °C    |

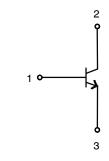
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



#### MARKING DIAGRAM



#### ELECTRICAL CONNECTION



#### **ORDERING INFORMATION**

| Device    | Package                  | Shipping        |
|-----------|--------------------------|-----------------|
| 2SC6144SG | TO-220F-3FS<br>(Pb-Free) | 50 Units / Tube |

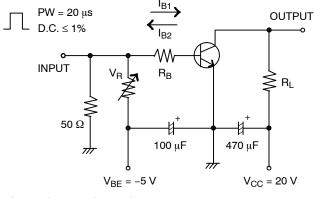
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#### **ELECTRICAL CHARACTERISTICS** at Ta = $25^{\circ}C$

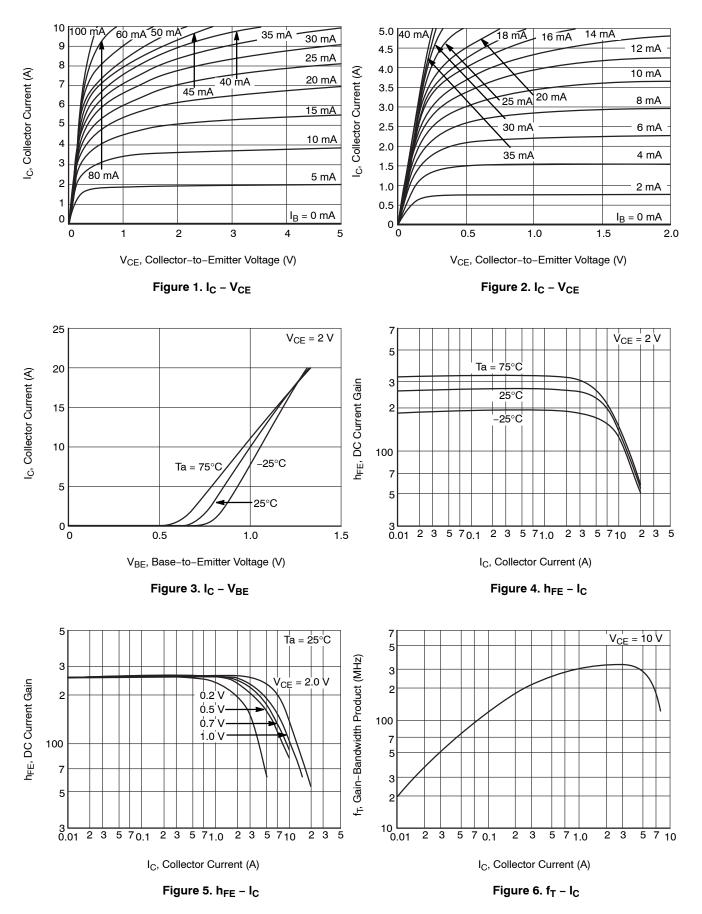
|   |                       |  | Ratings |     |     |       |
|---|-----------------------|--|---------|-----|-----|-------|
| Parameter                               | Symbol                | Conditions                                     | Min     | Тур | Max | Units |
| Collector Cutoff Current                | I <sub>CBO</sub>      | V <sub>CB</sub> = 40 V, I <sub>E</sub> = 0 A   | -       | -   | 10  | μA    |
| Emitter Cutoff Current                  | I <sub>EBO</sub>      | V <sub>EB</sub> = 4 V, I <sub>C</sub> = 0 A    | -       | -   | 10  | μA    |
| DC Current Gain                         | h <sub>FE</sub>       | V <sub>CE</sub> = 2 V, I <sub>C</sub> = 270 mA | 200     | -   | 560 |       |
| Gain-Bandwidth Product                  | f <sub>T</sub>        | V <sub>CE</sub> = 10 V, I <sub>C</sub> = 3 A   | -       | 330 | -   | MHz   |
| Output Capacitance                      | Cob                   | V <sub>CB</sub> = 10 V, f = 1 MHz              | -       | 60  | -   | pF    |
| Collector-to-Emitter Saturation Voltage | V <sub>CE</sub> (sat) | I <sub>C</sub> = 6 A, I <sub>B</sub> = 300 mA  | -       | 180 | 360 | mV    |
| Base-to-Emitter Saturation Voltage      | V <sub>BE</sub> (sat) | I <sub>C</sub> = 6 A, I <sub>B</sub> = 300 mA  | -       | -   | 1.2 | V     |
| Collector-to-Base Breakdown Voltage     | V <sub>(BR)CBO</sub>  | I <sub>C</sub> = 100 μA, I <sub>E</sub> = 0 A  | 60      | -   | -   | V     |
| Collector-to-Emitter Breakdown Voltage  | V <sub>(BR)CEO</sub>  | I <sub>C</sub> = 1 mA, R <sub>BE</sub> = ∞     | 50      | -   | -   | V     |
| Emitter-to-Base Breakdown Voltage       | V <sub>(BR)EBO</sub>  | I <sub>E</sub> = 100 μA, I <sub>C</sub> = 0 A  | 5       | -   | -   | V     |
| Turn-On Time                            | t <sub>ON</sub>       | See specified Test Circuit.                    | -       | 62  | -   | ns    |
| Storage Time                            | t <sub>stg</sub>      |  | -       | 350 | -   | ns    |
| Fall Time                               | t <sub>f</sub>        | 1  | -       | 25  | -   | ns    |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

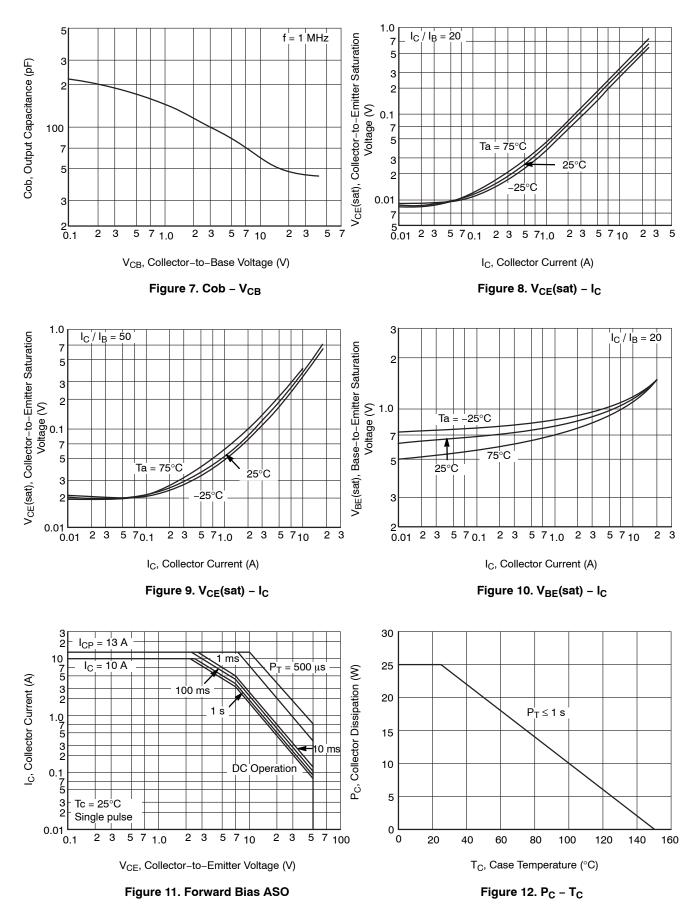
#### Switching Time Test Circuit



 $I_{C} = 20 I_{B1} = -20 I_{B2} = 5 A$ 



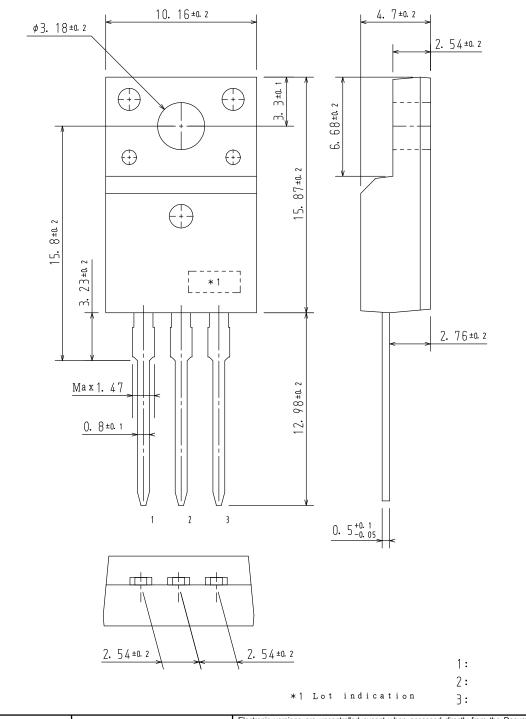
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TO-220F-3FS CASE 221AM ISSUE O

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| DESCRIPTION:     | TO-220F-3FS |   | PAGE 1 OF 1 |  |

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